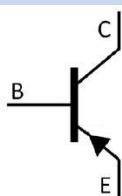


TO-92(R) PNP Silicon PNP transistor in a TO-92(R) Plastic Package.

High Voltage, Low Noise.

General purpose and switching application.

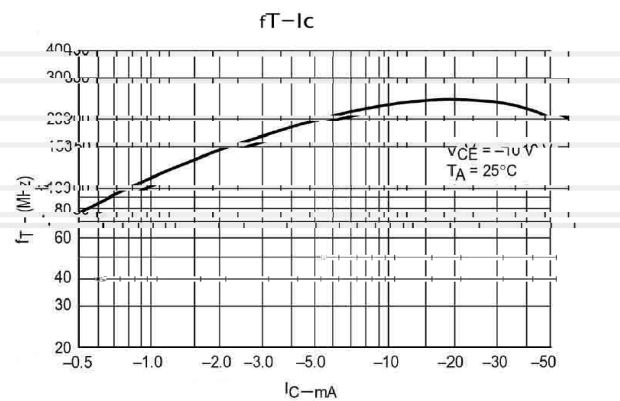
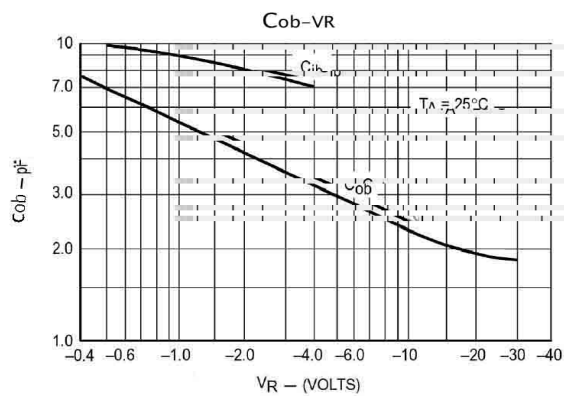
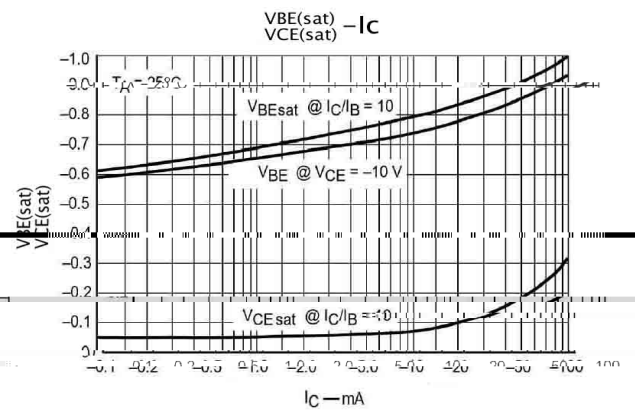
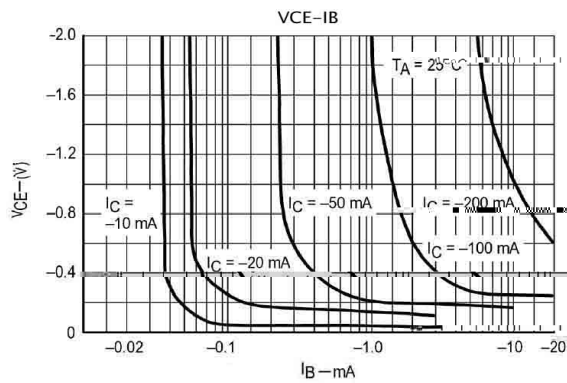
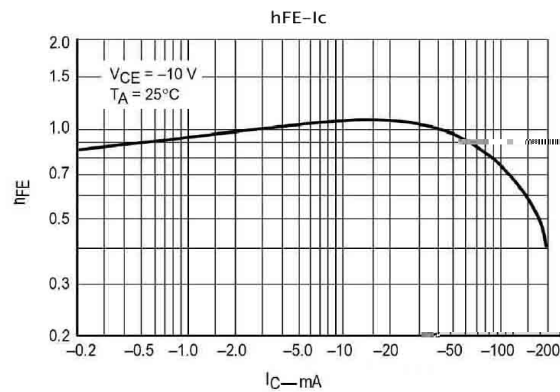


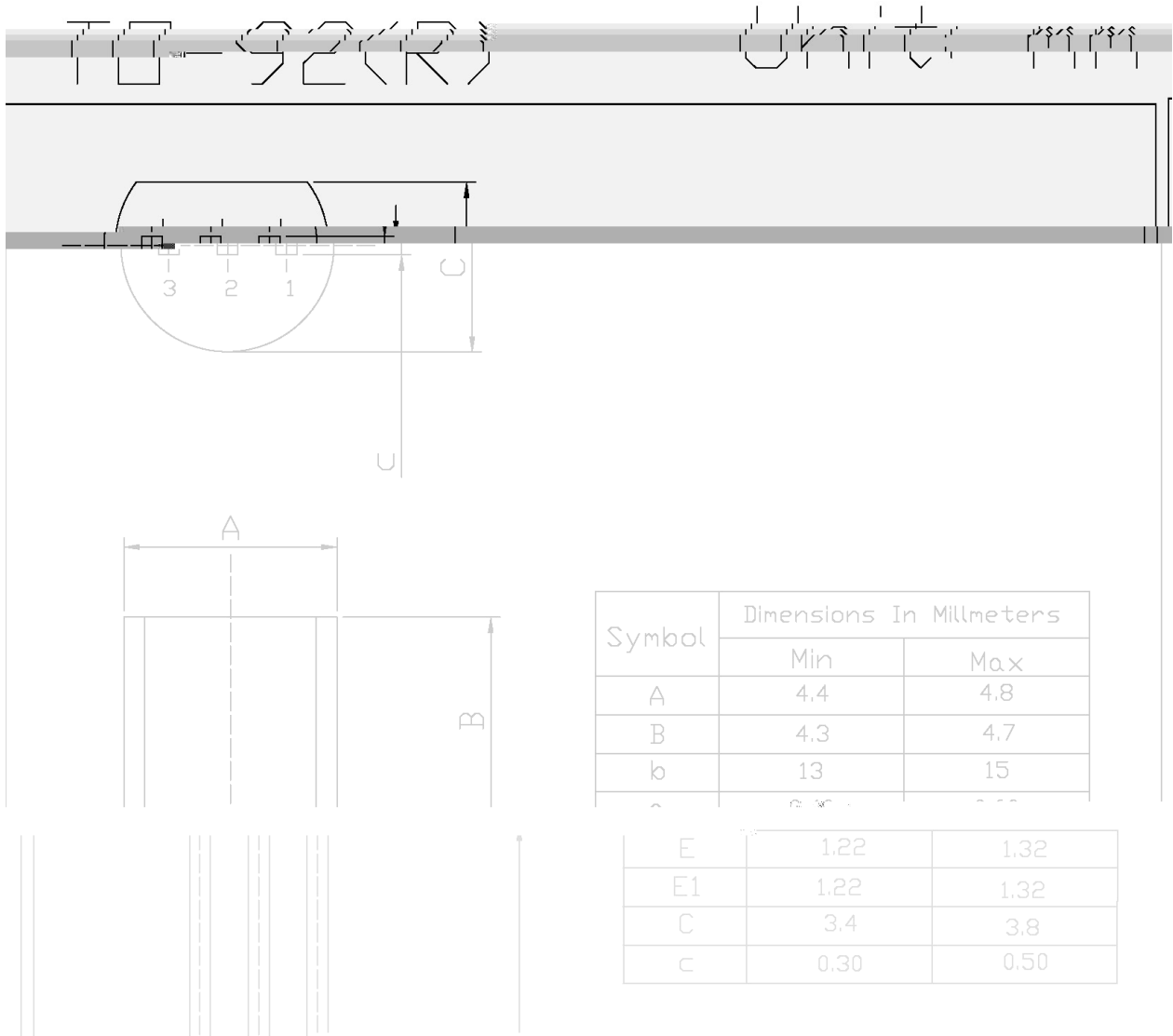
PIN1 Emitter PIN 2 Base PIN 3 Collector

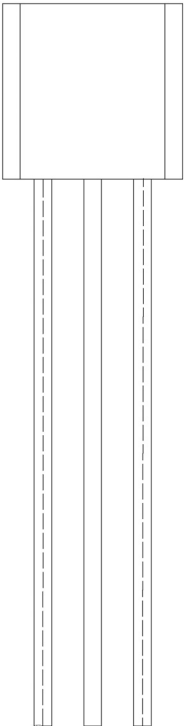
h_{FE} Classifications Symbol	A	B	C
h_{FE} Range	125 250	220 475	420 800

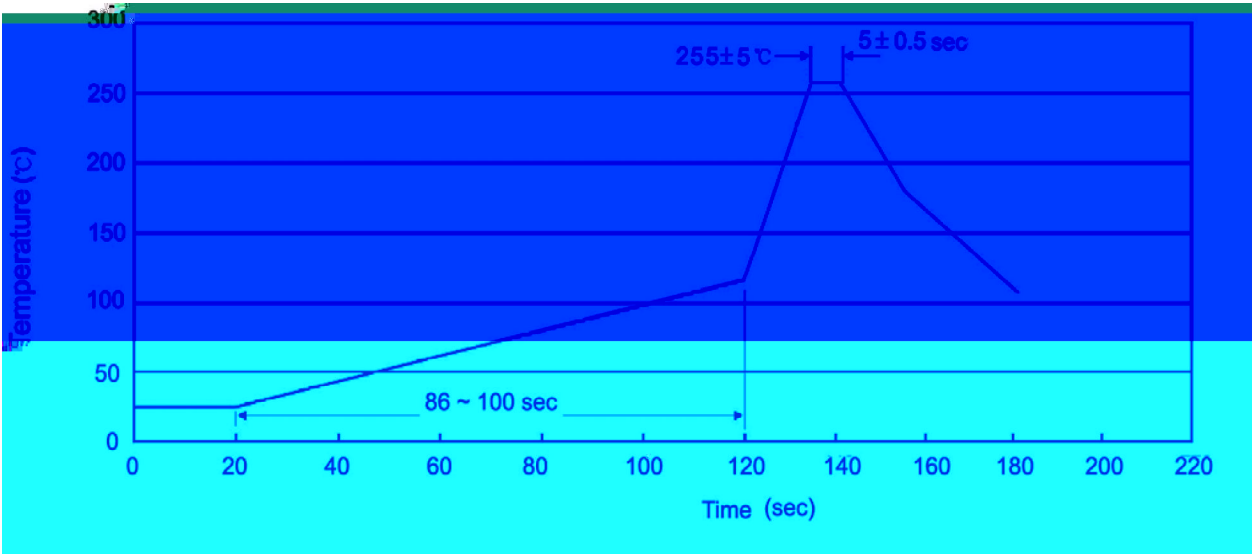
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Emitter Current - Continuous	I_E	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.015	μA
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-2.0mA$	125		800	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-5.0mA$			-0.65	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.9	-1.1	V
Base-Emitter Voltage	$V_{BE(1)}$	$V_{CE}=-5.0V$ $I_C=-2.0mA$	-0.6		-0.75	V
	$V_{BE(2)}$	$V_{CE}=-5.0V$ $I_C=-10mA$			-0.8	V
Current Gain Bandwidth Product	f_T	$V_{CE}=-5.0V$ $I_C=-10mA$ $f=100MHz$		150		MHz
Transition Frequency	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$		4.5		pF
Noise Figure	NF	$V_{CE}=-6.0V$ $I_C=-0.1mA$ $R_g=10K\Omega$ $f=1.0KHz$		1.0	10	dB









Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱